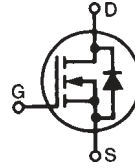


Polar™ HiperFET™ Power MOSFET

IXFR26N120P

$V_{DSS} = 1200V$
 $I_{D25} = 15A$
 $R_{DS(on)} \leq 550m\Omega$
 $t_{rr} \leq 300ns$

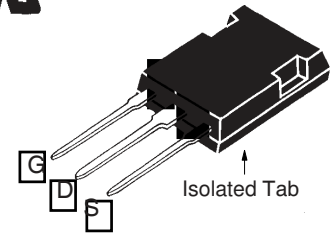
(Electrically Isolated Tab)



N-Channel Enhancement Mode
Fast Intrinsic Rectifier
Avalanche Rated

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ C$ to $150^\circ C$	1200	V
V_{DGR}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GS} = 1M\Omega$	1200	V
V_{GSS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	$T_C = 25^\circ C$	15	A
I_{DM}	$T_C = 25^\circ C$, Pulse Width Limited by T_{JM}	60	A
I_A	$T_C = 25^\circ C$	13	A
E_{AS}	$T_C = 25^\circ C$	1.5	J
dv/dt	$I_S \leq I_{DM}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ C$	15	V/ns
P_D	$T_C = 25^\circ C$	320	W
T_J		-55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		-55 ... +150	$^\circ C$
T_L	Maximum Lead Temperature for Soldering	300	$^\circ C$
T_{SOLD}	Plastic Body for 10s	260	$^\circ C$
V_{ISOL}	50/60 Hz, 1 Minute	2500	V~
F_C	Mounting Force	20..120/4.5..27	N/lb
Weight		5	g

ISOPLUS247
E153432



G = Gate D = Drain
S = Source

Features

- Silicon Chip on Direct-Copper Bond (DCB) Substrate
- Isolated Mounting Surface
- Low Intrinsic Gate Resistance
- 2500V~ Electrical Isolation
- International Standard Package
- Fast Recovery Rectifier
- Avalanche Rated
- Low Package Inductance

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

- High Voltage Switch-mode and Resonant-Mode Power Supplies
- High Voltage Pulse Power Applications
- High Voltage Discharge Circuits in Lasers Pulsers, Spark Igniters, RF Generators
- High Voltage DC-DC Converters
- High Voltage DC-AC Inverters

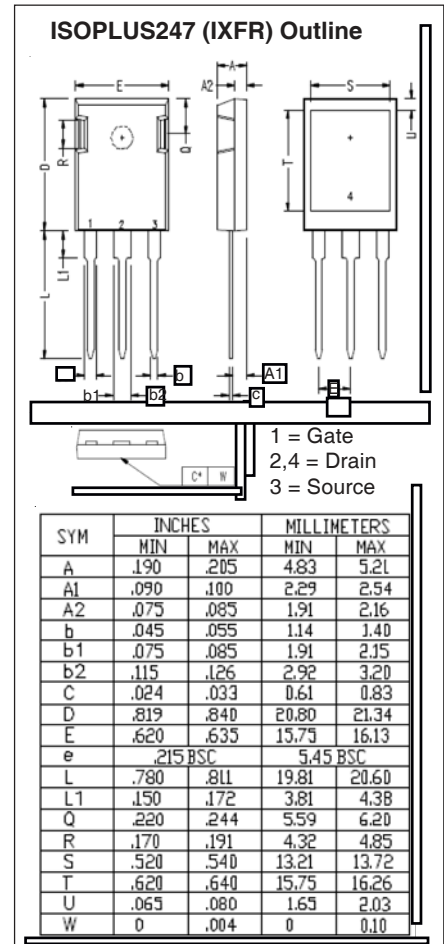
Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V$, $I_D = 3mA$	1200		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 1mA$	3.5		6.5 V
I_{GSS}	$V_{GS} = \pm 30V$, $V_{DS} = 0V$			± 200 nA
I_{DSS}	$V_{DS} = V_{DSS}$, $V_{GS} = 0V$ $T_J = 125^\circ C$			50 μA 5 mA
$R_{DS(on)}$	$V_{GS} = 10V$, $I_D = 13A$, Note 1			550 m Ω

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 20\text{V}, I_D = 13\text{A}$, Note 1	13	21	S
C_{iss}	$V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$		14	nF
C_{oss}			725	pF
C_{rss}			50	pF
R_{Gi}	Gate Input Resistance		1.5	Ω
$t_{d(on)}$	Resistive Switching Times $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 13\text{A}$ $R_G = 1\Omega$ (External)		56	ns
t_r			55	ns
$t_{d(off)}$			76	ns
t_f			58	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 13\text{A}$		225	nC
Q_{gs}			87	nC
Q_{gd}			98	nC
R_{thJC}				0.39°C/W
R_{thCS}		0.15		$^\circ\text{C/W}$

Source-Drain Diode

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
I_s	$V_{GS} = 0\text{V}$			26 A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			104 A
V_{SD}	$I_F = I_s, V_{GS} = 0\text{V}$, Note 1			1.5 V
t_{rr}	$I_F = 13\text{A}, -di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}, V_{GS} = 0\text{V}$			300 ns
Q_{RM}			1.3	μC
I_{RM}			12.0	A

Note 1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.



IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

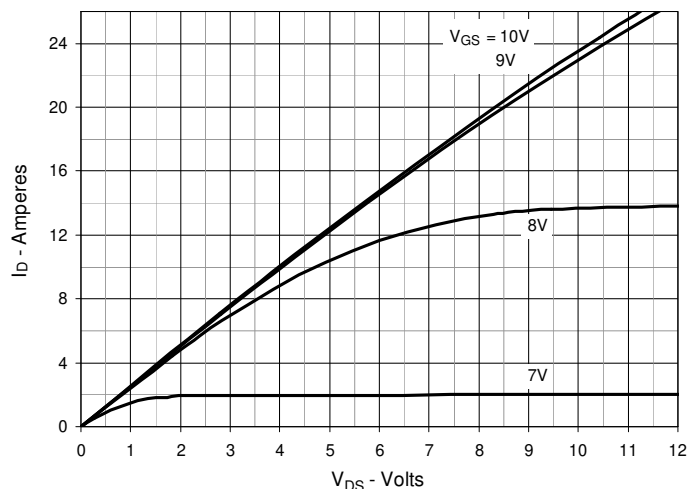
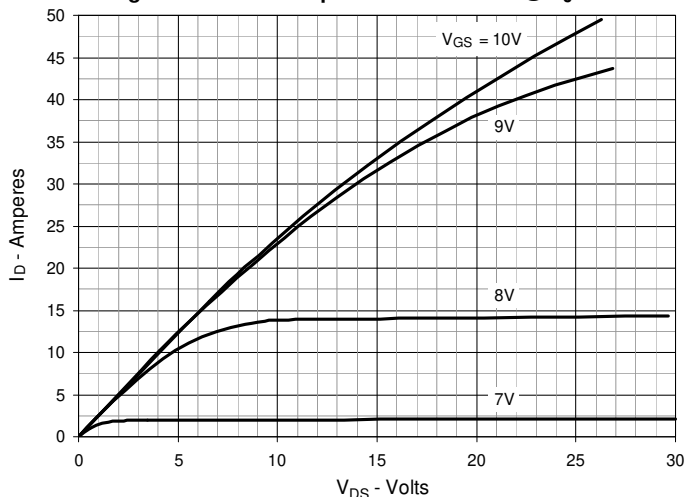
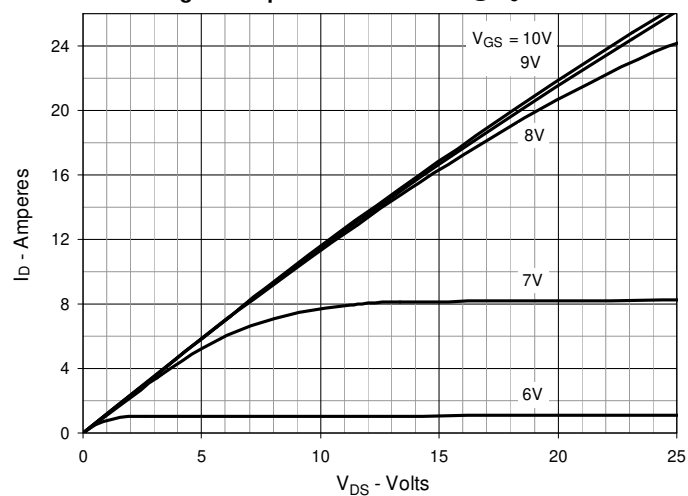
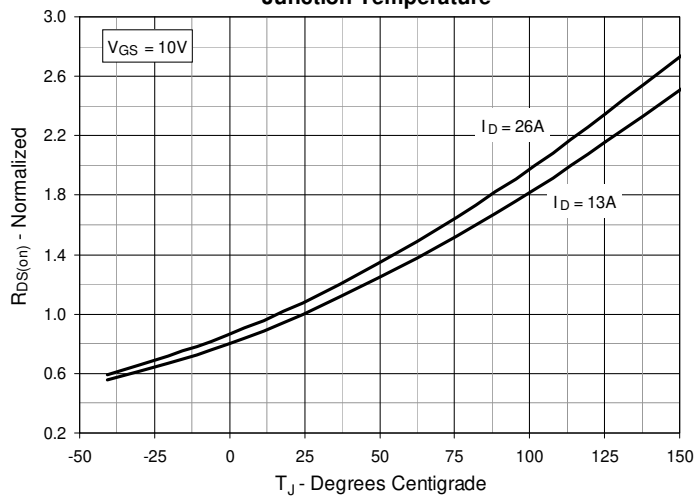
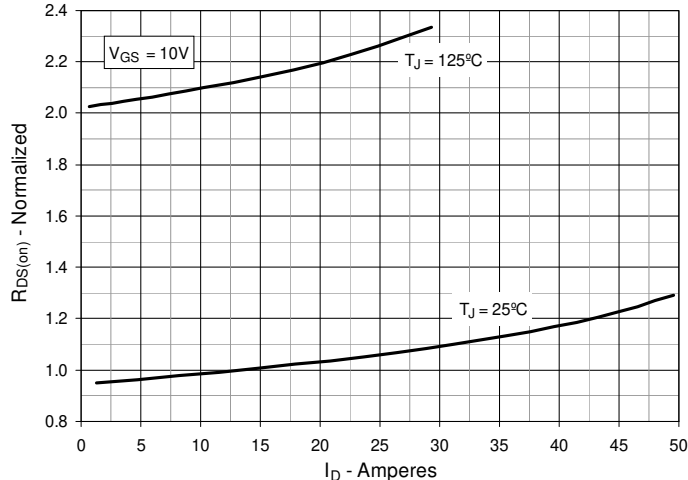
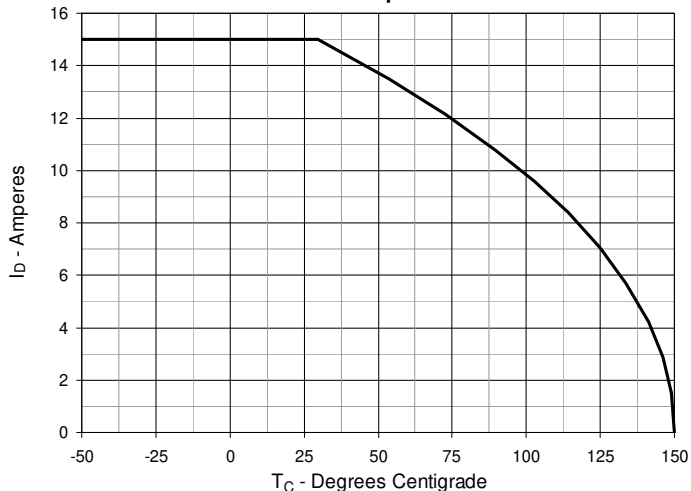
Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 13\text{A}$ Value vs. Junction Temperature

Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 13\text{A}$ Value vs. Drain Current

Fig. 6. Maximum Drain Current vs. Case Temperature


Fig. 7. Input Admittance

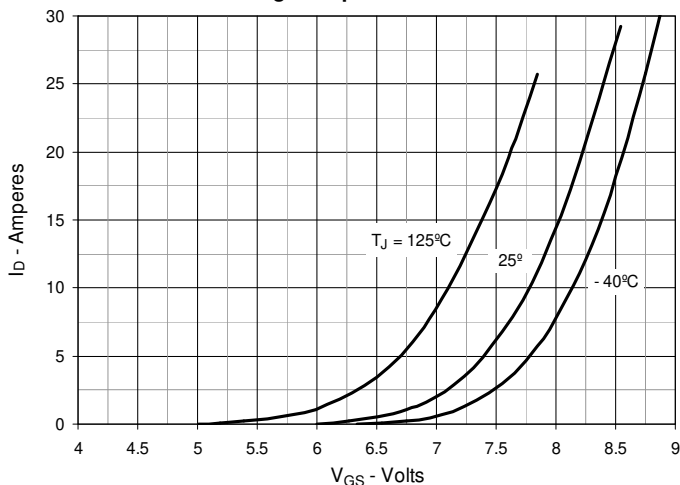


Fig. 8. Transconductance

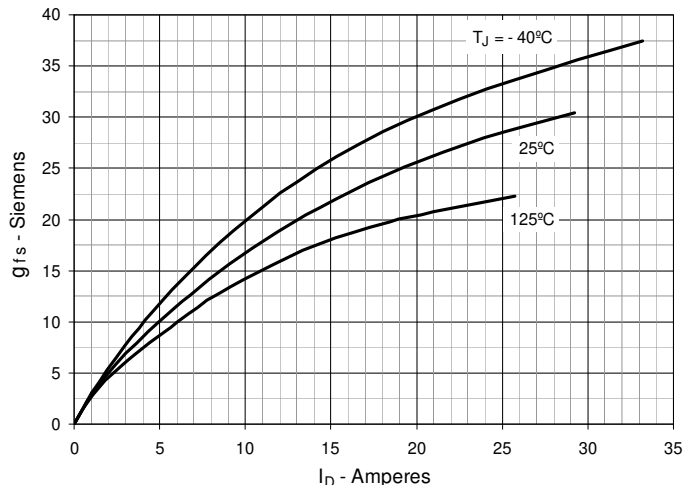


Fig. 9. Forward Voltage Drop of Intrinsic Diode

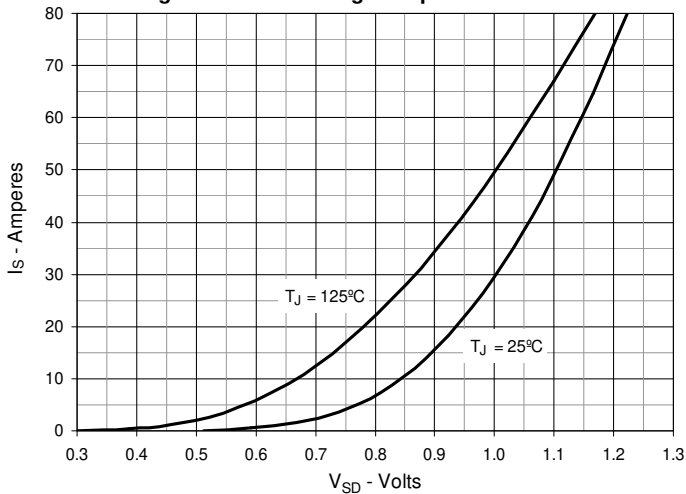


Fig. 10. Gate Charge

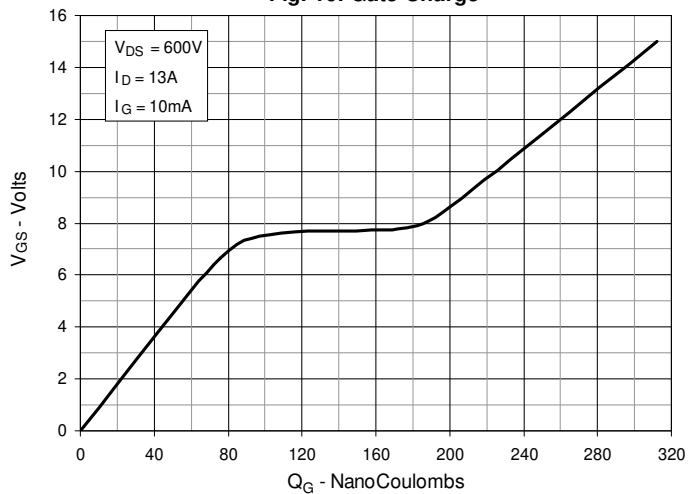


Fig. 11. Capacitance

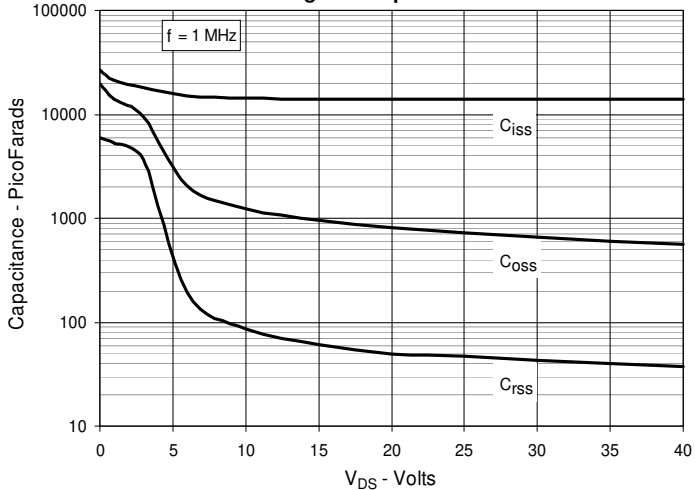
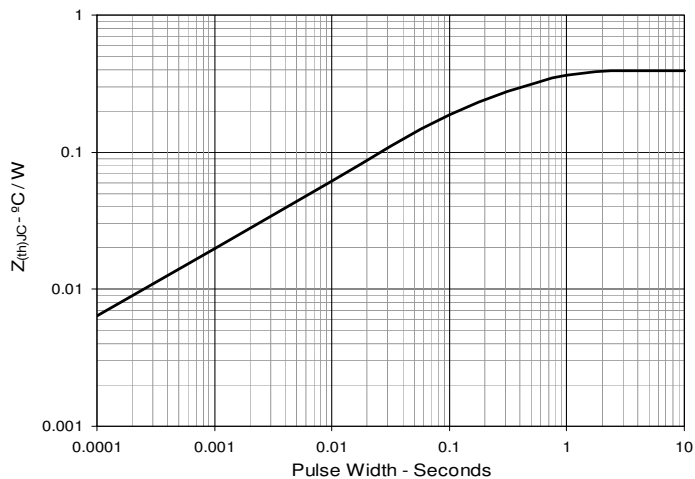


Fig. 12. Maximum Transient Thermal Impedance





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